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Fairchild Semiconductor 2N5830

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Discrete POWER & Signal **Technologies**

2N5830



NPN General Purpose Amplifier

This device is designed for general purpose high voltage amplifiers and gas discharge display driving. Sourced from Process 16. See 2N5551 for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	100	V
V _{CBO}	Collector-Base Voltage	120	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	200	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N5830	1
P _D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
R _{eJC}	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.



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NPN General Purpose Amplifier

(continued)

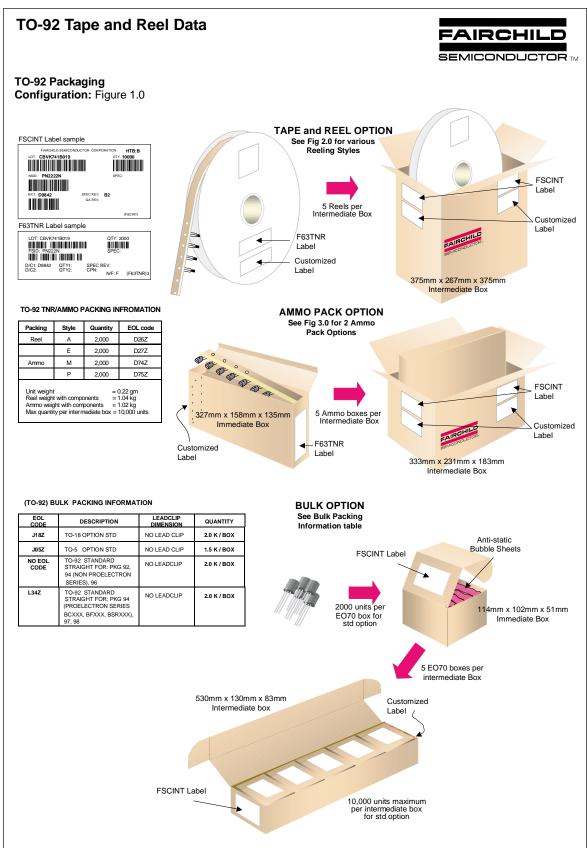
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	100		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	120		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0		V
I _{CBO}	Collector Cutoff Current	$V_{CB} = 100 \text{ V}, I_{E} = 0$		50	nA
I _{EBO}	Emitter Cutoff Current	$V_{CB} = 100 \text{ V}, I_{E} = 0, T_{A} = 100 ^{\circ}\text{C}$ $V_{EB} = 4.0 \text{ V}, I_{C} = 0$		25 50	μA nA
h _{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CF} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$	60 80	500	
		02		000	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 50 \text{ mA}$ $I_{C} = 1.0 \text{ mA}, I_{B} = 0.1 \text{ mA}$ $I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA}$	80	0.15 0.2	V
V _{CE} (sat)	Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage	$\begin{split} &V_{CE} = 5.0 \text{ V, } I_{C} = 50 \text{ mA} \\ &I_{C} = 1.0 \text{ mA, } I_{B} = 0.1 \text{ mA} \\ &I_{C} = 10 \text{ mA, } I_{B} = 1.0 \text{ mA} \\ &I_{C} = 50 \text{ mA, } I_{B} = 5.0 \text{ mA} \\ &I_{C} = 1.0 \text{ mA, } I_{B} = 0.1 \text{ mA} \\ &I_{C} = 10 \text{ mA, } I_{B} = 1.0 \text{ mA} \end{split}$	80	0.15	
	· ·	$\begin{split} &V_{CE} = 5.0 \text{ V, } I_{C} = 50 \text{ mA} \\ &I_{C} = 1.0 \text{ mA, } I_{B} = 0.1 \text{ mA} \\ &I_{C} = 10 \text{ mA, } I_{B} = 1.0 \text{ mA} \\ &I_{C} = 50 \text{ mA, } I_{B} = 5.0 \text{ mA} \\ &I_{C} = 1.0 \text{ mA, } I_{B} = 0.1 \text{ mA} \end{split}$	80	0.15 0.2 0.25 0.8 1.0	V V V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$\begin{split} &V_{CE} = 5.0 \text{ V, } I_{C} = 50 \text{ mA} \\ &I_{C} = 1.0 \text{ mA, } I_{B} = 0.1 \text{ mA} \\ &I_{C} = 10 \text{ mA, } I_{B} = 1.0 \text{ mA} \\ &I_{C} = 50 \text{ mA, } I_{B} = 5.0 \text{ mA} \\ &I_{C} = 1.0 \text{ mA, } I_{B} = 0.1 \text{ mA} \\ &I_{C} = 10 \text{ mA, } I_{B} = 1.0 \text{ mA} \\ &I_{C} = 50 \text{ mA, } I_{B} = 5.0 \text{ mA} \end{split}$	1.0	0.15 0.2 0.25 0.8 1.0 1.0	V V V V
V _{BE(sat)} V _{BE(on)} SMALL SI C _{cb} D _{fe}	Base-Emitter Saturation Voltage Base-Emitter On Voltage GNAL CHARACTERISTICS Output Capacitance Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V, } I_C = 50 \text{ mA} \\ &I_C = 1.0 \text{ mA, } I_B = 0.1 \text{ mA} \\ &I_C = 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ &I_C = 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ &I_C = 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ &I_C = 1.0 \text{ mA, } I_B = 0.1 \text{ mA} \\ &I_C = 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ &I_C = 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ &V_{CE} = 5.0 \text{ V, } I_C = 1.0 \text{ mA} \\ \end{split}$		0.15 0.2 0.25 0.8 1.0 1.0 0.8	V V V V V V PF
V _{BE(sat)} V _{BE(on)} SMALL SI	Base-Emitter Saturation Voltage Base-Emitter On Voltage IGNAL CHARACTERISTICS Output Capacitance	$\begin{split} &V_{CE} = 5.0 \text{ V, } I_C = 50 \text{ mA} \\ &I_C = 1.0 \text{ mA, } I_B = 0.1 \text{ mA} \\ &I_C = 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ &I_C = 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ &I_C = 50 \text{ mA, } I_B = 0.1 \text{ mA} \\ &I_C = 1.0 \text{ mA, } I_B = 0.1 \text{ mA} \\ &I_C = 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ &I_C = 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ &V_{CE} = 5.0 \text{ V, } I_C = 1.0 \text{ mA} \\ \end{split}$		0.15 0.2 0.25 0.8 1.0 1.0 0.8	V V V V V

^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

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Datasheet of 2N5830 - TRANS NPN 100V 0.2A TO-92

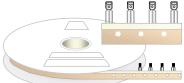
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TO-92 Tape and Reel Data, continued

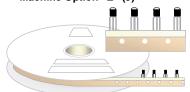
TO-92 Reeling Style Configuration: Figure 2.0





Style "A", D26Z, D70Z (s/h)

Machine Option "E" (J)

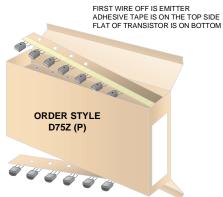


Style "E", D27Z, D71Z (s/h)

TO-92 Radial Ammo Packaging Configuration: Figure 3.0



ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON BOTTOM

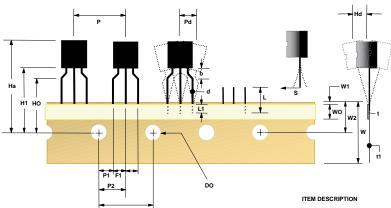


FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP



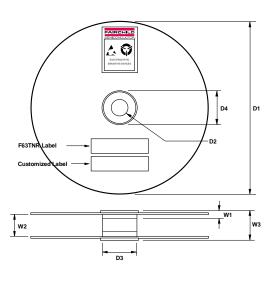
TO-92 Tape and Reel Data, continued

TO-92 Tape and Reel Taping Dimension Configuration: Figure 4.0



User Direction of Feed

TO-92 Reel Configuration: Figure 5.0



ITEM DESCRIPTION	SYMBOL	DIMENSION
Base of Package to Lead Bend	b	0.098 (max)
Component Height	Ha	0.928 (+/- 0.025)
Lead Clinch Height	HO	0.630 (+/- 0.020)
Component Base Height	H1	0.748 (+/- 0.020)
Component Alignment (side/side)	Pd	0.040 (max)
Component Alignment (front/back)	Hd	0.031 (max)
Component Pitch	P	0.500 (+/- 0.020)
Feed Hole Pitch	PO	0.500 (+/- 0.008)
Hole Center to First Lead	P1	0.150 (+0.009, -0.010)
Hole Center to Component Center	P2	0.247 (+/- 0.007)
Lead Spread	F1/F2	0.104 (+/- 0 .010)
Lead Thickness	d	0.018 (+0.002, -0.003)
Cut Lead Length	L	0.429 (max)
Taped Lead Length	L1	0.209 (+0.051, -0.052)
Taped Lead Thickness	t	0.032 (+/- 0.006)
Carrier Tape Thickness	t1	0.021 (+/- 0.006)
Carrier Tape Width	W	0.708 (+0.020, -0.019)
Hold - down Tape Width	WO	0.236 (+/- 0.012)
Hold - down Tape position	W1	0.035 (max)
Feed Hole Position	W2	0.360 (+/- 0.025)
Sprocket Hole Diameter	DO	0.157 (+0.008, -0.007)
Lead Spring Out	s	0.004 (max)

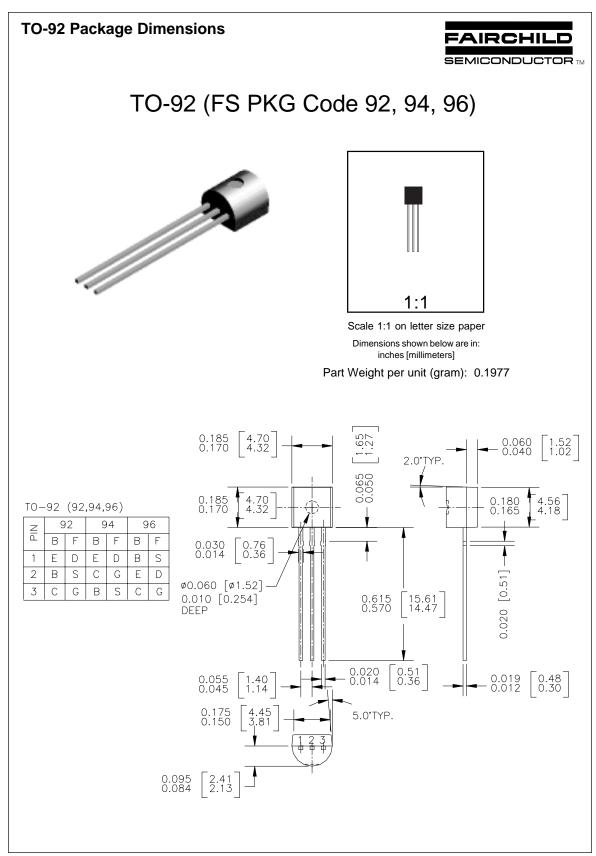
Note : All dimensions are in inches

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Note: All dimensions are inches



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